Intense, pulsed ion beams for studies of defect dynamics and materials processing very far from equilibrium

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### Intense, short ion pulses are a unique tools for (bio)-materials science, studies of phasetransitions and warm-dense matter research



- <u>Short</u> ion pulses enable access to dynamics of rad effects experiments
- <u>Intense</u> ion pulses enable access to phase transitions, materials processing far from equilibrium and warm dense matter with uniformly heated materials

- J. H. Bin, et al. Rev. Sci. Instr., in press (2019)
- P. A. Seidl, et al. Laser and Particle Beams 35, 373 (2017)
- J. J. Barnard, T. Schenkel, J. Appl. Phys. 122, 195901 (2017)
- A. Persaud, et al., Physics Procedia 66, 604 (2015)
- P. A. Seidl, et al., Nucl. Instr. Meth. B 800, 98 (2015)
- J. Schwartz et al., J. Appl. Phys. 116, 214107 (2014)

### **1.** Accelerators for intense, short ion pulses

- 1. Induction linac, NDCX-II
- 2. Laser-plasma acceleration, BELLA

### 2. Experiments with ion pulses at Berkeley Lab

- 1. Defect dynamics
- 2. Materials processing and color center synthesis
- 3. Phase transitions





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### Intense, pulsed ion beams by neutralized drift compression in an induction linac – NDCX-II



• NDCX-II at Berkeley Lab





- 1.1 MeV (He<sup>+</sup>), 12 nC (7.5x10<sup>10</sup> ions), 13 mJ
- Routinely ~5x10<sup>11</sup> ions/cm<sup>2</sup>/pulse
- Pulse length: 2 to 10 ns, spot size ~1 to 5 mm radius, 1 MeV protons, He<sup>+</sup>, Li<sup>+</sup>, ...
- Peak current: ~0.1 to 2 A
- Repetition rate ~1 shot / minute







# Pulses of 1 MeV protons from NDCX-II



- Proton pulses with peak currents of 0.1 to 1 A, 10 to 20 ns FWHM, ~1 to 5E10 protons/pulse (to date)
- The proton energy is 1 MeV with a range in silicon of 16 um.
- J-H Bin, et al., Rev. Sci. Instr., in press (2019)







### We use the BELLA PW laser to form pulses of high energy electrons (GeV) and ions (MeV)

- BELLA 1 PW at 1 Hz
- 40 J, 33 fs, ~2x10<sup>19</sup> W/cm<sup>2</sup>
- The BELLA Center is part of a network of collaborative user facilities, LaserNetUS (www.LaserNetUS.org)
- Contacts:
  - T\_Schenkel@LBL.gov
  - CGRGeddes@lbl.gov







**BELLA** overview: K. Nakamura et al., IEEE J. Quant. Electr. 53, 1200121 (2017)

#### A. J. Gonsalves, et al. Phys. Rev. Lett. 122, 084801 (2019)







# Ion acceleration at BELLA-i









- ~10<sup>12</sup> total number of MeV ions (from Thomson parabola) and >10<sup>13</sup> lower energy ions (from ex situ sample analysis by Secondary Ion Mass Spectrometry, SIMS)
- Ti tape drive target for extended 1 Hz operation
- Bin et al. Rev. Sci. Instr., in press (2019); Steinke et al, in preparation

### Setup for laser ion acceleration at 1 Hz with samples 3 cm from the laser target



Target wheel for samples to be hit by ions

#### Laser pulse



Thomson parabola spectra of protons and carbon ions from a Kapton tape laser target

- Tape drive for laser targets, e.g. Kapton (shown) or titanium, ~2 – 10 micron thick
- Distance of laser-target to iontarget now 3 cm for proton fluences of 5 to 10 J/cm<sup>2</sup>/shot with sub-ns pulses





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### Motivation: Understanding the dynamics of radiation induced defects in solids

- Defects affect materials properties
  - Desired properties (e.g. optical, electrical, ...)
  - Undesired properties (e. g. mechanical failure, ...)
- Defect dynamics is a multi-scale problem (ps to years)
- Probes of defect dynamics on different time scales can inform the development of optimized materials and benchmark simulation models

(2012)



#### Efficient Annealing of Radiation Damage Near Grain Boundaries via Interstitial Emission

X.-M. Bai, A. F. Voter, R. G. Hoagland, M. Nastasi, B. P. Uberuaga, Science 327, 1631 (2010)



NV-Center

Effects of low-energy electron irradiation on formation of nitrogenvacancy centers in single crystal diamond J. Schwartz, S. Aloni, F. Ogletree, T. Schenkel, New J. Phys. 14 043024

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### NV-centers form during local exposure to low energy electrons at room temperature



• confocal PL image of NV<sup>-</sup> centers (635–642 nm) at room temperature, recorded following exposure of 1 µm squares to a 9 pA, 2 keV electron beam. Insets show locally auto-scaled spots.

#### local activation enables iterative formation of NV<sup>-</sup> in arrays

- Note: activation of NV<sup>0</sup> centers in diamond by low energy electrons and high energy ions was reported already in the 70s and 80s (see A. M. Zaitsev, 2001)
- J. Schwartz, S. Aloni, D. F. Ogletree and T. Schenkel, "Effects of low-energy electron irradiation on formation of nitrogen-vacancy centers in single-• crystal diamond", New J. Phys. 14, 043024 (2012)







# What are mechanisms of NV-formation?

 $N_{substitutional} + V \rightarrow NV^{0, -}$ 

VS.

 $N_{\text{interstitial}} + V_n \rightarrow NV^{0, -}$ 

J. Schwartz, et al., NJP 2012, JAP 2014



- A nitrogen atom on a split interstitial site (blue), close to two vacancies (black). Carbon atoms in yellow. NV's form during annealing at >300 °C
  - J. Adler, R. Kalish, et al., J. of Physics, 2014
- P. Deak et al. PRB 2014: di-vacancy formation favored over NV formation during annealing of N rich diamond after vacancy producing irradiation







# Short ion pulses enable access to the dynamics of radiation effects in pump-probe type experiments



# Time resolved detection of ion transmission through single crystal silicon membranes



Faraday Cup, ~2 ns time resolution



 $\Delta t$ : time between damage event and arrival of the next channeled ion in the same region





• 1 μm thick, Si (100)

### Order-disorder transition can be tracked *in situ* with ion channeling during short ion pulses







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### Materials processing – limits of conventional annealing





- Bismuth doped <sup>28</sup>Si enabled the recent demonstrations of the Purcell effect with spins
- But only ~60% of the bismuth atoms were electrically active after conventional processing
- $\rightarrow$  Excite materials locally with intense, pulsed ion beams and rapidly quench to stabilize the novel phase
- "Controlling spin relaxation with a cavity", 2. A. Bienfait, J. J. Pla, Y. Kubo, X. Zhou, M. Stern, C. C. Lo, C. D. Weis, T. Schenkel, D. Vion, D. Esteve, J. J. L. Morton, P. Bertet, Nature 531, 74 (2016)







#### First pulsed implantation of SiC with ion pulses from BELLA-i



### Exposure of semiconductor samples to proton pulses with ~1 to 10 J/cm<sup>2</sup> and PW laser shot rates up to 0.2 Hz – analysis in progress





• next step - focusing of ions onto a second target with a plasma lens - in progress







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# 3.Phase transitions









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https://www.lanl.gov/projects/dense-plasma-theory/background/warm-dense-matter.php





### Heating of thin tin foils (300 nm) with a short-pulse helium beam





P. A. Seidl, et al., Laser and Particle Beams (2017), 35, 373-378





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# HYDRA simulations show heating to warm dense matter by protons and carbon ions with ion pulse parameters in reach at BELLA



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